

216114US2SDIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF :
SOICHI INOUE ET AL : GROUP:
SERIAL NO.: NEW APPLICATION : EXAMINER:
FILED: HERewith :

FOR: PATTERN FORMING METHOD
AND PATTERN FORMING
APPARATUS

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
Washington, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified patent
application as follows:

IN THE SPECIFICATION

Please rewrite the specification as shown below.

Please replace the following paragraph beginning on page 1, line 24, with the
following text:

--Consider the case of forming a device pattern by first forming a master mask (a
photomask, an X-ray mask, an electron beam mask, an ion beam mask, etc.) for the device
pattern using a mask writing tool (which writes a pattern with an electron beam or a laser
beam), then radiating the master mask with electromagnetic waves such as light, an X-ray,
etc., or with charged particles such as an electron beam, an ion beam, etc. to thereby project

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M. F. Hedges

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